

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims

Claims 1-18 (Canceled)

Claim 19 (New): A transistor, comprising:

- a source/drain region;
- a buried strap out-diffusion region adjacent to one sidewall of a deep trench; and
- a bended gate, comprising a first portion extending along a first direction and a second portion extending along a second direction intersecting with the first direction, wherein the first portion of the bended gate is adjacent to the source/drain region and the second portion of bended gate is adjacent to the buried strap out-diffusion region.

Claim 20 (New): The transistor as claimed in claim 19, wherein the deep trench is a trench of a deep trench capacitor.

Claim 21 (New): The transistor as claimed in claim 19, wherein the bended gate is adjacent to a shallow trench isolation.

Claim 22 (New): The transistor as claimed in claim 19, further comprising a bit line contact electrically contacting the source/drain region.

Claim 23 (New): The transistor as claimed in claim 21, wherein a spacer is formed on a sidewall of the bended gate between the bit line contact and the bended gate.

Claim 24 (New): The transistor as claimed in claim 19, wherein the bended gate is L shaped.

Claim 25 (New): The transistor as claimed in claim 19, further comprising a bended gate oxide layer underlying the bended gate.

Claim 26 (New): The transistor as claimed in claim 19, wherein the first direction and the second direction are perpendicular.

Claim 27 (New): The transistor as claimed in claim 19, wherein the source/drain region is disposed in a substrate.

Claim 28 (New): The transistor as claimed in claim 27, wherein the first direction is parallel to the substrate surface.

Claim 29 (New): The transistor as claimed in claim 19, wherein the second direction is parallel to a sidewall of the trench.

Claim 30 (New): A memory device, comprising a deep trench capacitor and a transistor controlling the deep trench capacitor, wherein the transistor is as claimed in claim 19.